

| Radiation | Type | Technology | Electrodes |
|-----------|------|---------------|--------------|
| Infrared | DDH | AlGaAs/AlGaAs | P (anode) up |

| | | |
|---|--|--|
| <p style="text-align: center;">LED-07</p> | typ. dimensions (µm) | |
| | <u>typ. thickness</u> 180 µm <u>anode</u> gold alloy, 1.5 µm <u>cathode</u> gold alloy, 0.5 µm structured 25 % | |

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

| Parameter | Test conditions | Symbol | Min | Typ | Max | Unit |
|---------------------------|-------------------------|---------------------------------|-----|--------|-----|------|
| Forward voltage | I _F = 20 mA | V _F | 1.3 | 1.5 | 1.7 | V |
| Forward voltage | I _F = 100 mA | V _F | | 1.65 | | V |
| Reverse voltage | I _R = 100 µA | V _R | 5 | | | V |
| Radiant power* | I _F = 20 mA | Φ _e | 2.5 | 3.6 | | mW |
| Radiant power* | I _F = 100 mA | Φ _e | | 18 | | mW |
| Peak wavelength | I _F = 20 mA | λ _p | 750 | 765 | 780 | nm |
| Spectral bandwidth at 50% | I _F = 20 mA | Δλ _{0.5} | 20 | 35 | 50 | nm |
| Switching time | I _F = 20 mA | t _r , t _f | | 20, 30 | | ns |

*Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

| Type | Lot N° | Φ _e (typ) [mW] | V _F (typ) [V] | Quantity |
|------------|--------|---------------------------|--------------------------|----------|
| ELC-770-12 | | @ 20 mA | @ 20 mA | |

Packing: Chips on adhesive film with wire-bond side on top

Note: All measurements carried out with JENOPTIK Polymer Systems equipment

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.